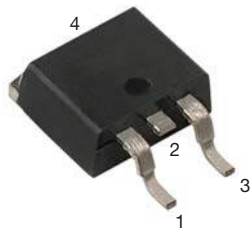
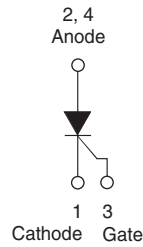


Thyristor Surface Mount, Phase Control SCR, 8 A


 TO-263AB (D²PAK)


FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Input rectification and crow-bar (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-12TTS08SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK)
Diode variation	Single SCR
$I_{T(AV)}$	8 A
V_{DRM}/V_{RRM}	800 V
V_{TM}	1.2 V
I_{GT}	15 mA
T_J	-40 to +125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	8	A
$I_{T(RMS)}$		12.5	
V_{RRM}/V_{DRM}		800	V
I_{TSM}		110	A
V_T	8 A, $T_J = 25$ °C	1.2	V
dV/dt		150	V/μs
dI/dt		100	A/μs
T_J	Range	-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-12TTS08SPbF	800	800	1.0



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	$I_{T(AV)}$	$T_C = 108\text{ }^\circ\text{C}$, 180° conduction, half sine wave		8	A
Maximum RMS on-state current	$I_{T(RMS)}$			12.5	
Maximum peak one-cycle non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$		95	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		110	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$		45	A^2s
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		64	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to } 10\text{ ms}$, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$		640	$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	8 A, $T_J = 25\text{ }^\circ\text{C}$		1.2	V
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$		16.2	$m\Omega$
Threshold voltage	$V_{T(TO)}$			0.87	V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.05	mA
		$T_J = 125\text{ }^\circ\text{C}$		1.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$		30	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max.}$, linear to 80 %, $V_{DRM} = R_g - k = \text{Open}$		150	$V/\mu s$
Maximum rate of rise of turned-on current	dI/dt			100	$A/\mu s$

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}			8.0	W
Maximum average gate power	$P_{G(AV)}$			2.0	
Maximum peak positive gate current	$+I_{GM}$			1.5	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$		20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$		1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		0.7	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$		0.2	
Maximum DC gate current not to trigger	I_{GD}			0.1	mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$		0.8	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$		3	
Typical turn-off time	t_q			100	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style D ² PAK (SMD-220)	12TTS08S	

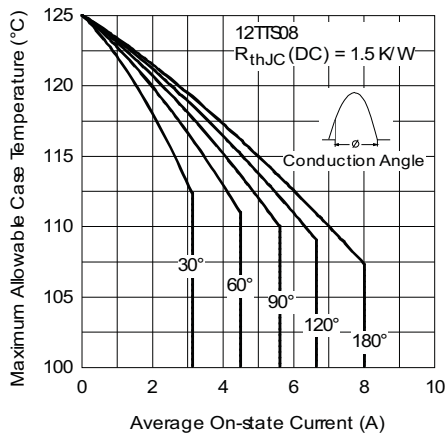


Fig. 1 - Current Rating Characteristics

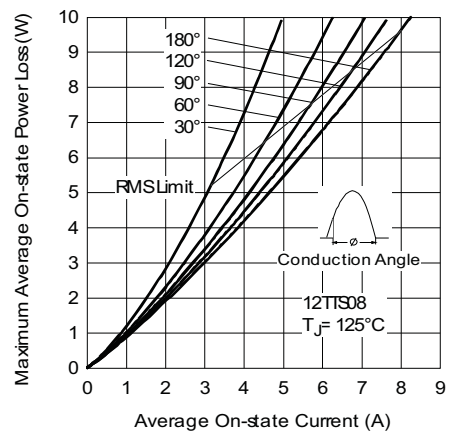


Fig. 3 - On-State Power Loss Characteristics

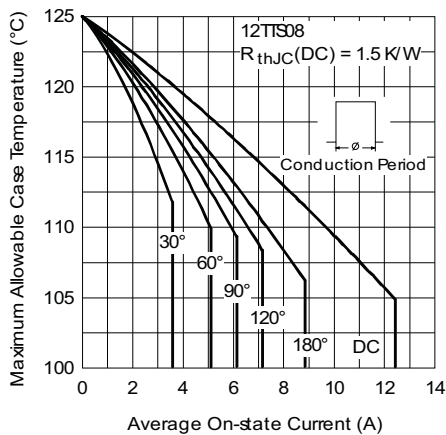


Fig. 2 - Current Rating Characteristics

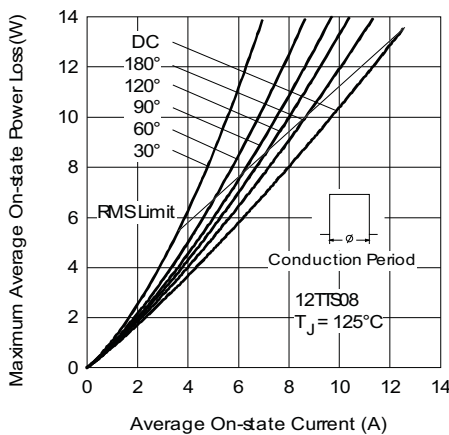


Fig. 4 - On-State Power Loss Characteristics

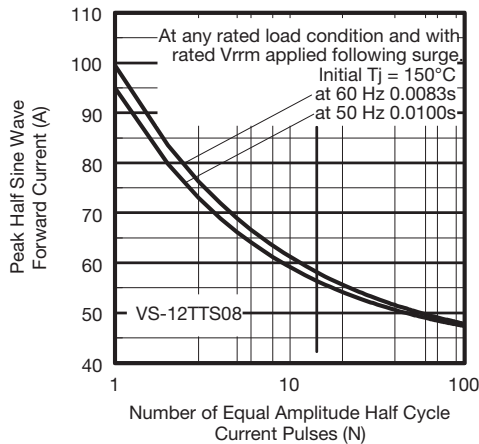


Fig. 5 - Maximum Non-Repetitive Surge Current

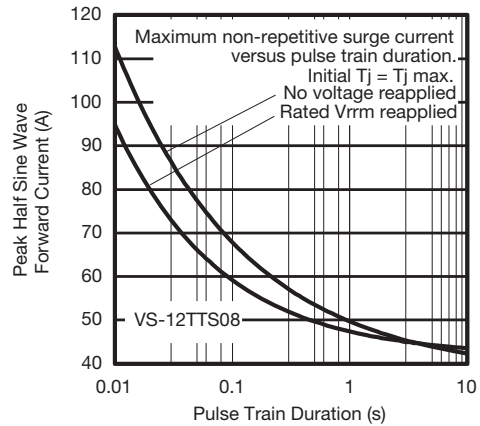


Fig. 6 - Maximum Non-Repetitive Surge Current

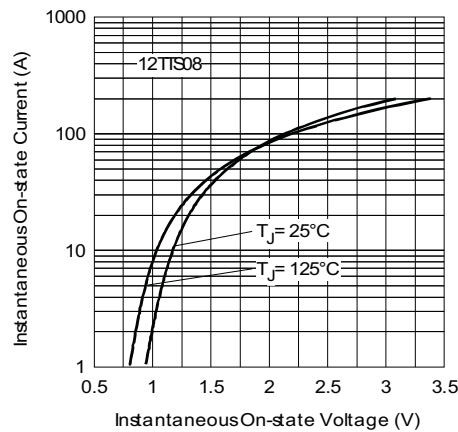


Fig. 7 - On-State Voltage Drop Characteristics

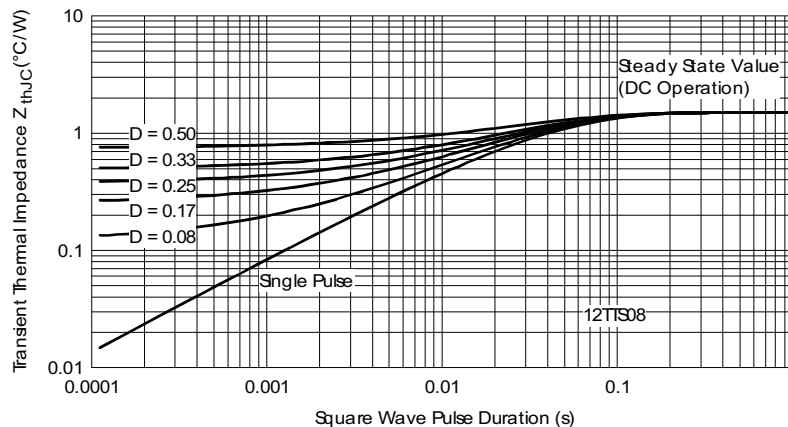


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code	VS-	12	T	T	S	08	S	TRL	PbF
	1	2	3	4	5	6	7	8	9

- 1** - Vishay Semiconductors product
- 2** - Current rating (12.5 A)
- 3** - Circuit configuration:
T = single thyristor
- 4** - Package:
T = TO-220AC
- 5** - Type of silicon:
S = standard recovery rectifier
- 6** - Voltage rating (08 = 800 V)
- 7** - S = TO-220 D²PAK (SMD-220) version
- 8** -
 - None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9** - PbF = lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-12TTS08SPbF	50	1000	Antistatic plastic tubes
VS-12TTS08STRRPbF	800	800	13" diameter reel
VS-12TTS08STRLPbF	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC® outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC® outline TO-263AB



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